

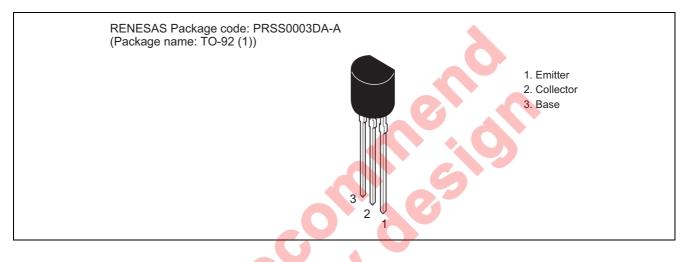
Silicon PNP Epitaxial

REJ03G0629-0200 (Previous ADE-208-316) Rev.2.00 Aug.10.2005

Application

Low frequency low noise amplifier

Outline



Absolute Maximum Ratings

 $(Ta = 25^{\circ}C)$

			(1a = 25 C)
Item	Symbol	Ratings	Unit
Collector to base voltage	V _{CBO}	-55	V
Collector to emitter voltage	V _{CEO}	-55	V
Emitter to base voltage	V _{EBO}	-5	V
Collector current	Ι _C	-100	mA
Emitter current	Ι _Ε	100	mA
Collector power dissipation	Pc	200	mW
Junction temperature	Tj	150	°C
Storage temperature	Tstg	-55 to +150	°C



Electrical Characteristics

							$(Ta = 25^{\circ}C)$
ltem	Symbol	Min	Тур	Max	Unit	Test conditions	
Collector to base breakdown voltage	V _{(BR)CBO}	-55	-	—	V	$I_{C} = -10 \ \mu A, \ I_{E} = 0$	
Collector to emitter breakdown voltage	V _{(BR)CEO}	-55	_	—	V	$I_{C} = -1 \text{ mA}, R_{BE} = \infty$	
Emitter to base breakdown voltage	V _{(BR)EBO}	-5	_	—	V	$I_E = -10 \ \mu A, \ I_C = 0$	
Collector cutoff current	I _{CBO}			-100	nA	$V_{CB} = -18 \text{ V}, I_E = 0$	
Emitter cutoff current	I _{EBO}		_	-50	nA	$V_{EB} = -2 V, I_C = 0$	
DC current transfer ratio	h _{FE} * ¹	160	_	500		$V_{CE} = -12 \text{ V}, \text{ I}_{C} = -2 \text{ mA}$	
Collector to emitter saturation voltage	V _{CE(sat)}		-0.1	-0.5	V	$I_{\rm C} = -10 \text{ mA}, I_{\rm B} = -1 \text{ mA}$	
Base to emitter voltage	V _{BE}		-0.66	-0.75	V	$V_{CE} = -12 \text{ V}, \text{ I}_{C} = -2 \text{ mA}$	
Gain bandwidth product	f⊤	_	200	—	MHz	$V_{CE} = -12 \text{ V}, I_E = -2 \text{ mA}$	
Collector output capacitance	Cob		2.0	_	pF	$V_{CB} = -10 \text{ V}, I_E = 0, f = 1 \text{MHz}$	
Noise figure	NF		1	5	dB	$V_{CE} = -6 V,$	f = 10 Hz
		—	0.5	1	dB	l _C = –0.1mA, R _g = 10 kΩ	f = 1 kHz

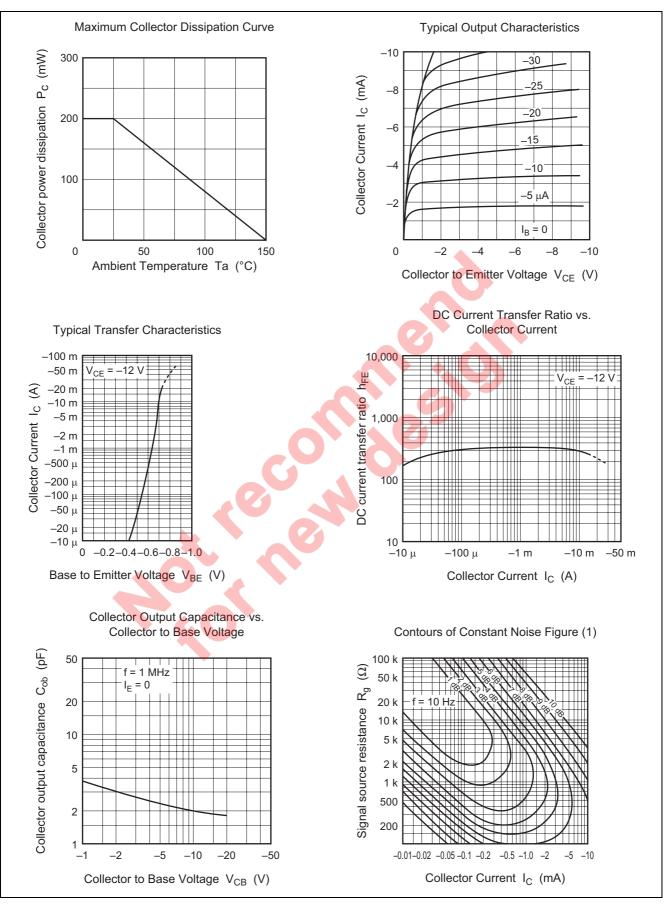
Note: 1. The 2SA836 is grouped by h_{FE} as follows.

С	D		
160 to 320	250 to 500		

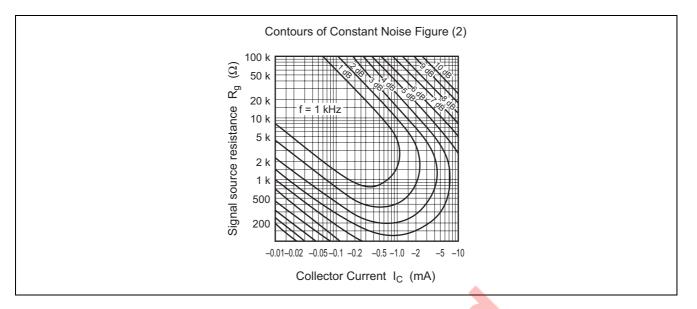
Rev.2.00 Aug 10, 2005 page 2 of 5



Main Characteristics

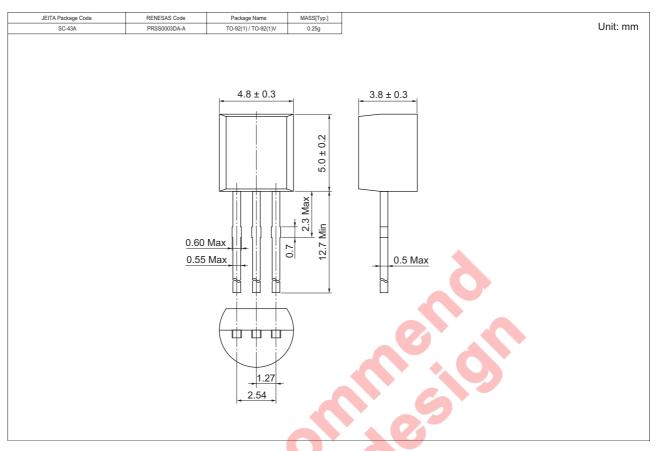








Package Dimensions



Ordering Information

Part Name	Quantity	Shipping Container
2SA836CTZ	2500	Hold Box, Radial Taping
2SA836DTZ		

Note: For some grades, production may be terminated. Please contact the Renesas sales office to check the state of production before ordering the product.



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